

Customer No.: 31561
Application No.: 10/604,761
Docket No.: 9886-US-PA

IN THE SPECIFICATION

Please amend the specification as follows.

[0030] Referring to Fig. 2D, an implantation process 208 is performed using the photoresist layer 205 as a mask for forming a source 202a and a drain 202b in the regions 201a and 201c of the polysilicon layer 202 respectively, and at the same time, an LDD 203 is formed in the polysilicon layer 202 underneath the edge portion 205b of the photoresist layer 205. The portion of the polysilicon layer between the source/drain 202a/202b and the LDD 203 is a channel region 202c of the device. In the embodiment, the ion concentration in the source/drain 202a/202b is, for example, 1×10^{14} to 1×10^{15} ~~ions/cm³~~ ~~ions/cm²~~, the ion concentration in the LDD 203 is, for example, 1×10^{12} to 1×10^{14} ~~ions/cm³~~ ~~ions/cm²~~, and the width of the LDD 203 is, for example, 0.1 to 1 μm .

[0035] Referring to Fig. 4C, an implantation process 308 is performed using the photoresist layer 305 as a mask for forming a source 310a and a drain 310b in the first region 301a of the substrate 300, and at the same time, an LDD 312 is formed in the substrate 300 underneath the edge portion 305b of the patterned photoresist layer 305. In the preferred embodiment of the present invention, the ion concentration in the source/drain 302a/302b is, for example, 1×10^{13} to 1×10^{16} ~~ions/cm³~~ ~~ions/cm²~~, the ion concentration in the LDD 312 is, for example, 1×10^{12} to 1×10^{15} ~~ions/cm³~~ ~~ions/cm²~~, and the LDD 312 is formed in a width of, for example, 0.01 to 0.1 μm .